imall

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Panasonic

MOS FET FCAB21520L1

FCAB21520L1

Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

Features

- Source-source ON resistance:RSS(on) typ. = 1.6 m Ω (VGS = 3.8 V)
- CSP(Chip Size Package)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1)
- Marking Symbol: 7T

Packaging

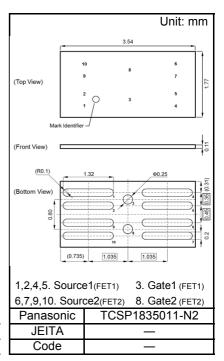
Embossed type (Thermo-compression sealing): 1 000 pcs / reel (standard)

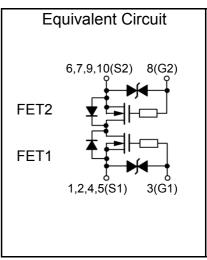
Absolute Maximum Ratings Ta = 25 °C								
Parameter		Symbol	Rating	Unit				
Source-source Voltage		VSS	12	V				
Gate-source Voltage		VGS	±8	V				
Source Current	DC ^{*1}	IS1	16	А				
	DC ^{*2}	IS2	35	А				
	Pulse *3	ISp	160	Α				
Total Power Dissipation	DC ^{*1}	PD1	0.54	W				
Total Power Dissipation	DC ^{*2}	PD2	3.8	W				
Channel Temperature		Tch	150	°C				
Storage Temperature Range		Tstg	-55 to +150	°C				
Thermal Resistance (ch-a)		Rth ^{*1}	232	°C/W				
		Rth ^{*2}	33	°C/W				

Note *1 Mounted on FR4 board (25.4 mm \times 25.4 mm \times t1.0 mm) using the minimum recommended pad size (36 μm Copper).

*2 Mounted on Ceramic substrate (70 mm \times 70 mm \times t1.0 mm).

*3 t = 10 $\mu s,$ Duty Cycle \leq 1 %







MOS FET FCAB21520L1

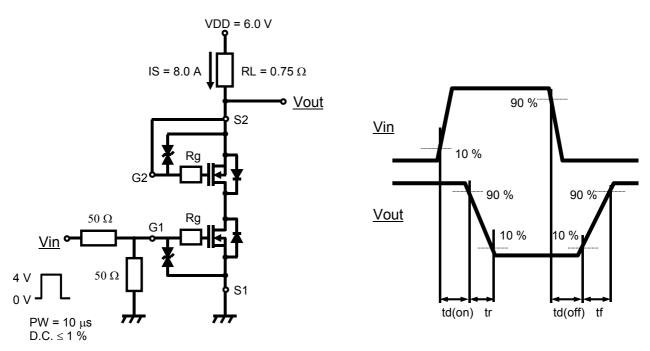
■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Source-source Breakdown Voltage	VSSS	IS = 1.0 mA, VGS = 0 V	12			V	
Zero Gate Voltage Source Current	ISSS	VSS = 12 V, VGS = 0 V			1.0	μA	
Gate-source Leakage Current	IGSS	VGS = ±8 V, VSS = 0 V			±10		
	1000	VGS = ±5 V, VSS = 0 V			±1.0	μA	
Gate-source Threshold Voltage	Vth	IS = 1.64 mA, VSS = 10 V	0.35	0.90	1.40	V	
Source-source On-state Resistance	RSS(on)1	IS = 8.0 A, VGS = 4.5 V	1.1	1.45	2.0	mΩ	
	RSS(on)2	IS = 8.0 A, VGS = 3.8 V	1.15	1.6	2.1		
	RSS(on)3	IS = 8.0 A, VGS = 3.1 V	1.2	1.8	3.0		
	RSS(on)4	IS = 8.0 A, VGS = 2.5 V	1.4	2.3	4.5		
Body Diode Forward Voltage	VF(s-s)	IF = 8.0 A, VGS = 0 V		0.7	1.2	V	
Input Capacitance *1	Ciss			5250		pF	
Output Capacitance ^{*1}	Coss	VSS = 10 V, VGS = 0 V, f = 1 kHz		700			
Reverse Transfer Capacitance ^{*1}	Crss			630			
Turn-on Delay Time *1,*2	td(on)	VDD = 6.0 V, VGS = 0 to 4.0 V		1.5		μs	
Rise Time ^{*1,*2}	tr	IS = 8.0 A		2.6			
Turn-off Delay Time *1,*2	td(off)	VDD = 6.0 V, VGS = 4.0 to 0 V		6.8		μs	
Fall Time *1,*2	tf	IS = 8.0 A		4.1			
Total Gate Charge ^{*1}	Qg	VDD = 6.0 V		38			
Gate-source Charge ^{*1}	Qgs	VGS = 0 to 4.0 V		20		nC	
Gate-drain Charge ^{*1}	Qgd	IS = 8.0 A		10			

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

*1 Guaranteed by design, not subject to production testing

*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

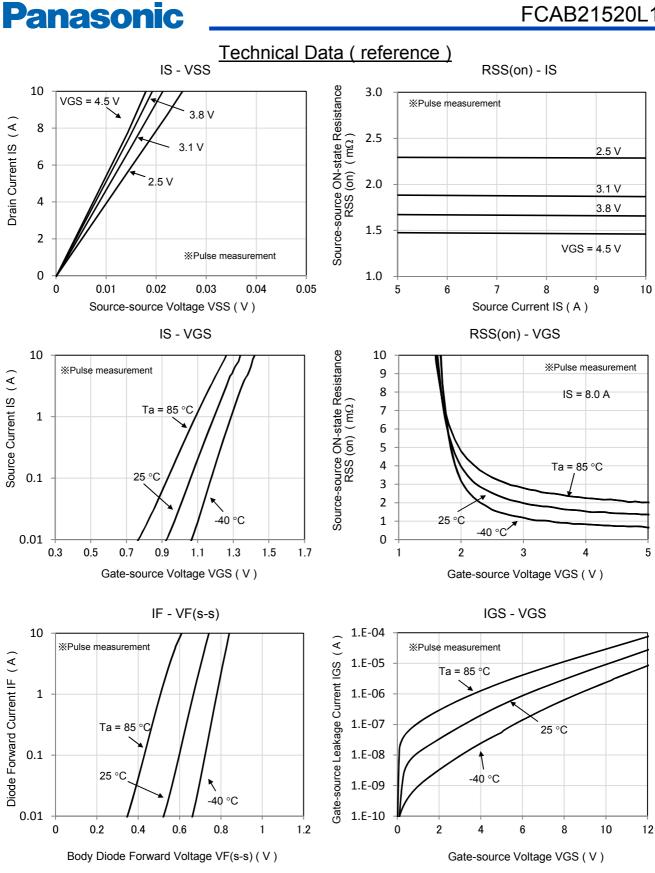


Note2:Measurement circuit

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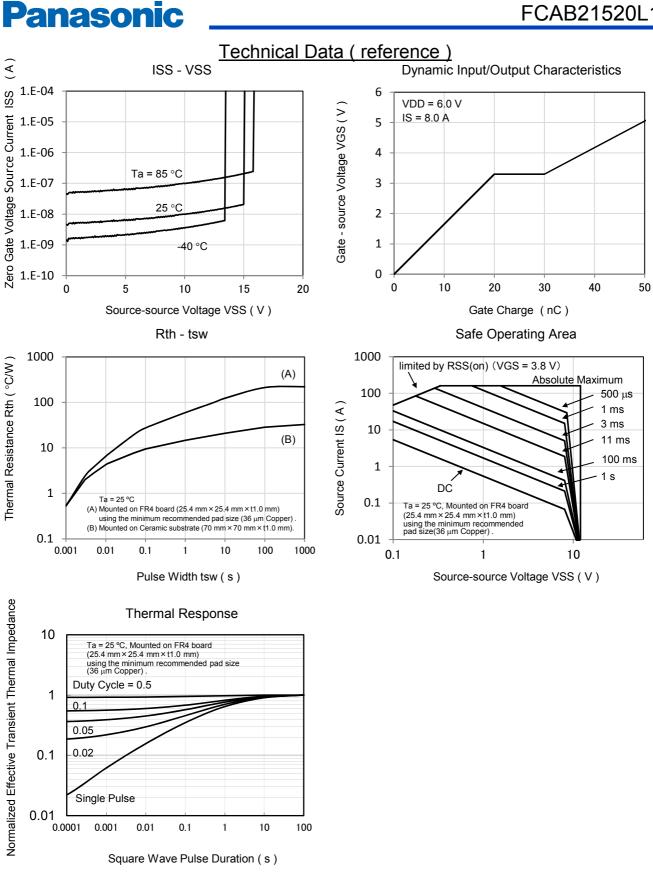
MOS FET FCAB21520L1



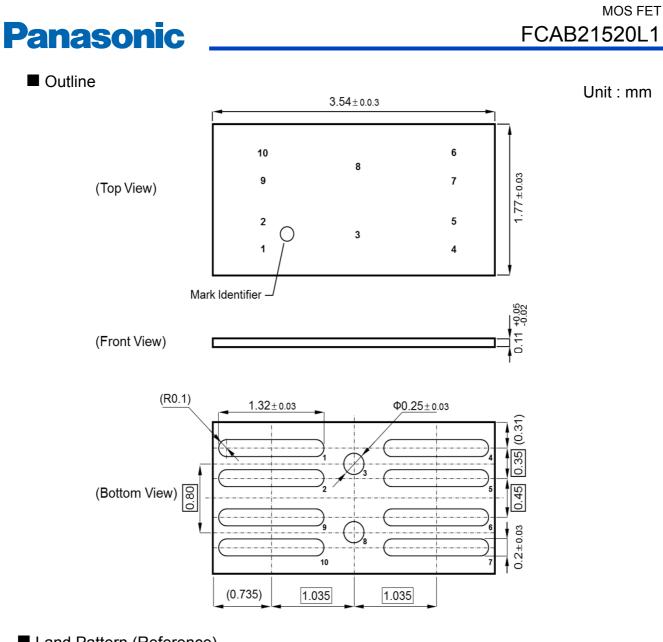
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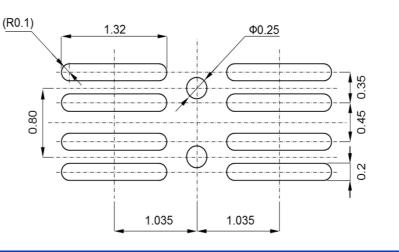
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■ Land Pattern (Reference)



Unit : mm

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